



BUK9217-75B

N-channel TrenchMOS logic level FET

Rev. 02 — 3 February 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

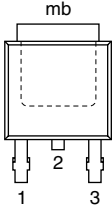
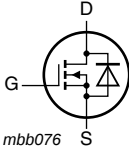
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	-	75	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see Figure 1 ; see Figure 3	-	-	64	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	167	W
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	13.4	15	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see Figure 10 ; see Figure 11	-	14.4	17	mΩ
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 64 A; V _{sup} ≤ 75 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	-	147	mJ
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 60 V; T _i = 25 °C; see Figure 12	-	14	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT428 (DPAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK9217-75B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 185\text{ }^{\circ}\text{C}$	-	75	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	75	V
V_{GS}	gate-source voltage		-15	15	V
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 5\text{ V}$; see Figure 1 ; see Figure 3	-	64	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 5\text{ V}$; see Figure 1	-	45	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 3	-	256	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; see Figure 2	-	167	W
T_{stg}	storage temperature		-55	185	$^{\circ}\text{C}$
T_j	junction temperature		-55	185	$^{\circ}\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	64	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	256	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 64\text{ A}$; $V_{sup} \leq 75\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; unclamped	-	147	mJ

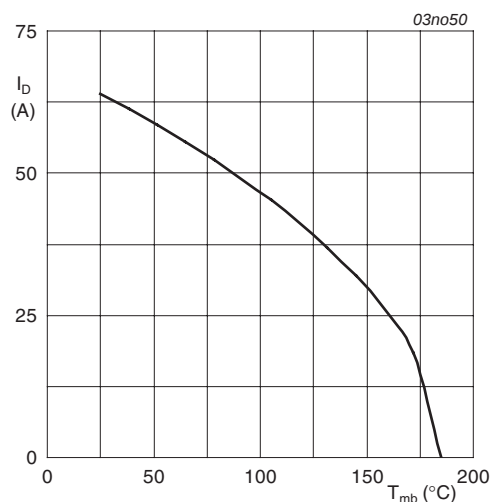
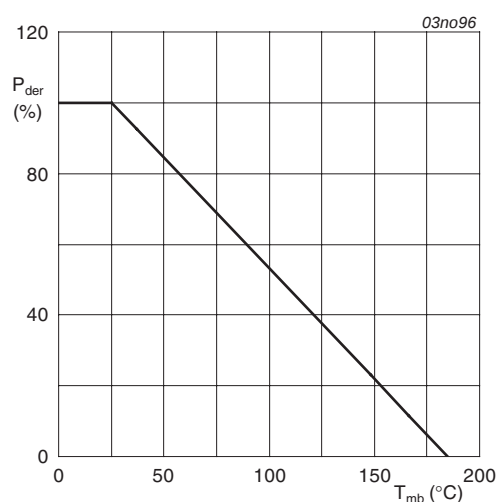


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

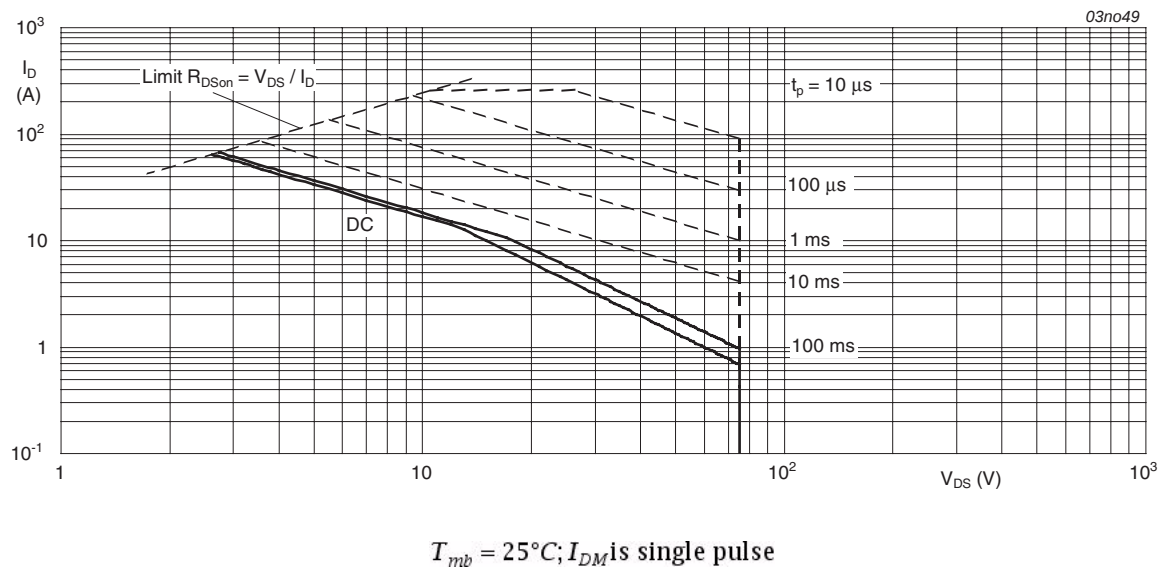


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W

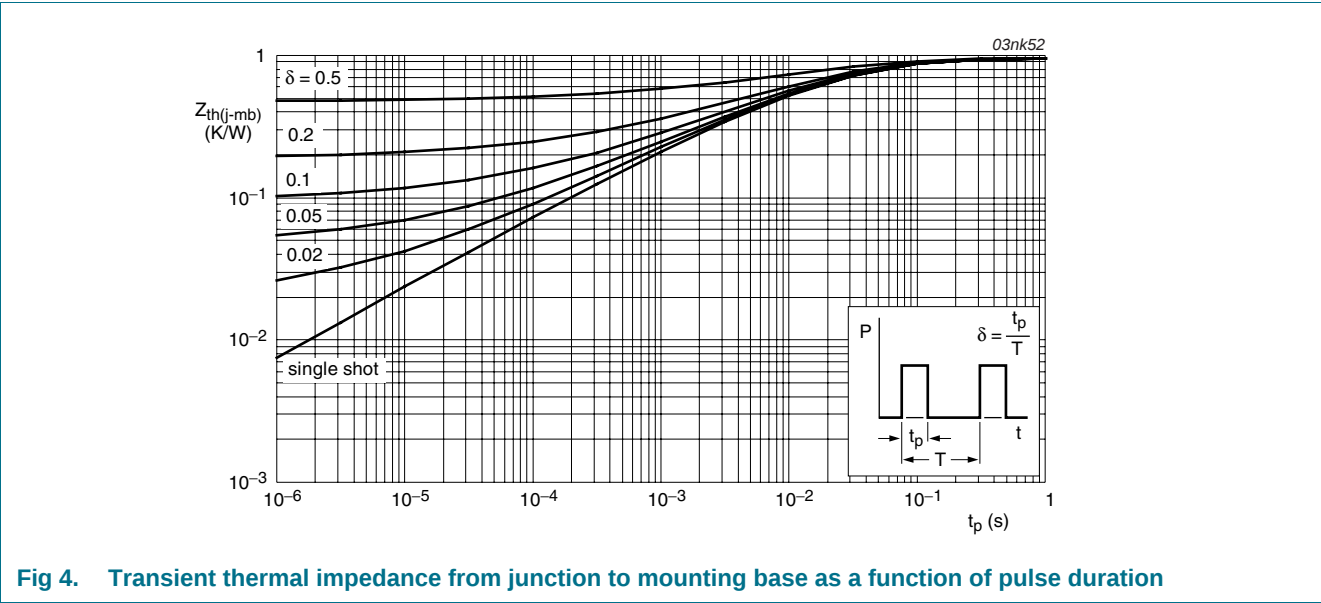
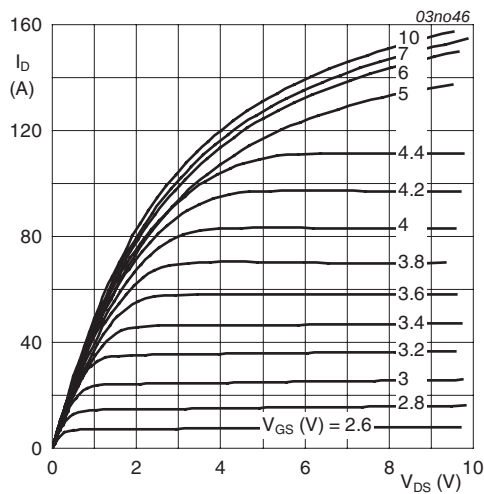


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

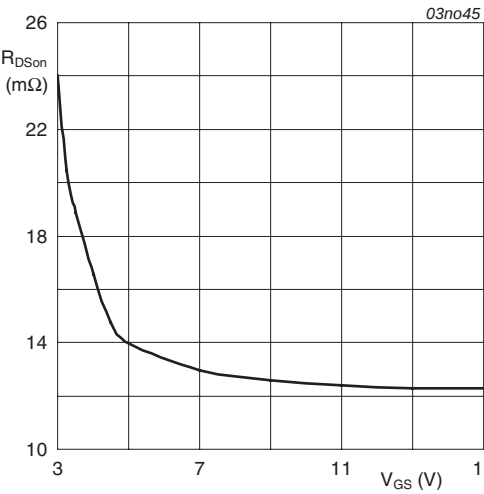
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	75	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	70	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see Figure 9	1.1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 185 °C; see Figure 9	0.4	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see Figure 9	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 75 V; V _{GS} = 0 V; T _j = 185 °C	-	-	500	μA
		V _{DS} = 75 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
I _{GSS}	gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	19	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 185 °C; see Figure 10 ; see Figure 11	-	-	40	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	13.4	15	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see Figure 10 ; see Figure 11	-	14.4	17	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 60 V; V _{GS} = 5 V; T _j = 25 °C; see Figure 12	-	35	-	nC
Q _{GS}	gate-source charge		-	6	-	nC
Q _{GD}	gate-drain charge		-	14	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; see Figure 15	-	3022	4029	pF
C _{oss}	output capacitance		-	290	348	pF
C _{rss}	reverse transfer capacitance		-	115	158	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V; R _{G(ext)} = 10 Ω; T _j = 25 °C	-	30	-	ns
t _r	rise time		-	102	-	ns
t _{d(off)}	turn-off delay time		-	101	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain inductance	measured from drain to center of die ; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source lbond pad ; T _j = 25 °C	-	7.5	-	nH
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 13	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	96	-	ns
Q _r	recovered charge		-	138	-	nC



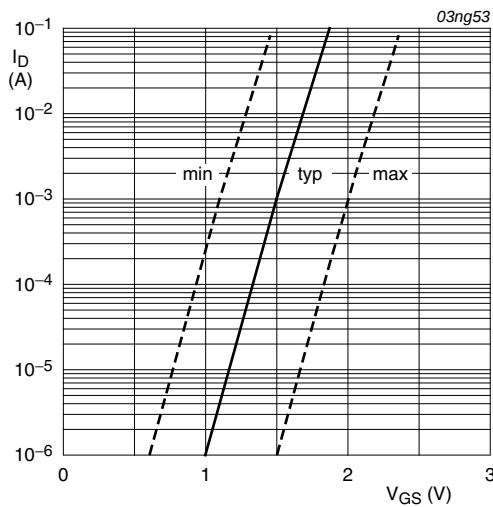
$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



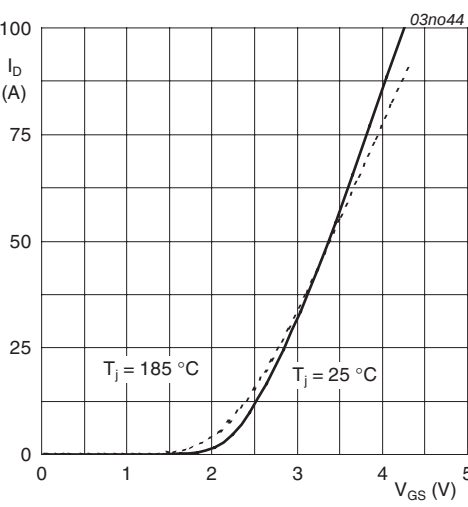
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



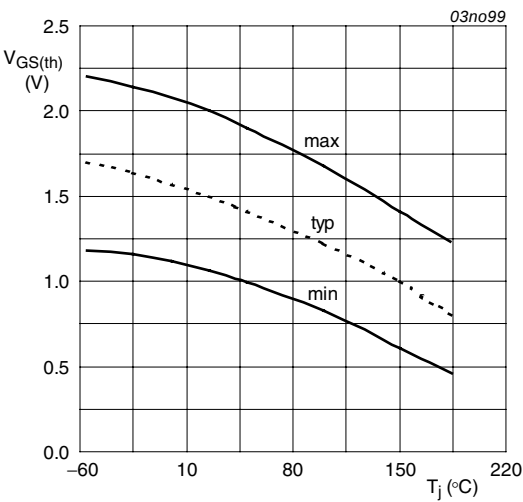
$T_j = 25^\circ\text{C}; V_{DS} = V_{GS}$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



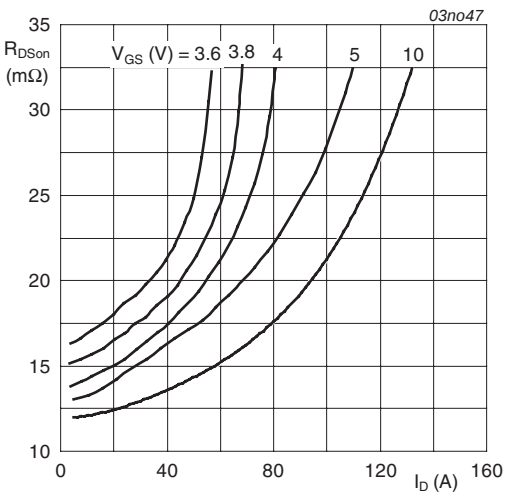
$V_{DS} = 25\text{V}$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



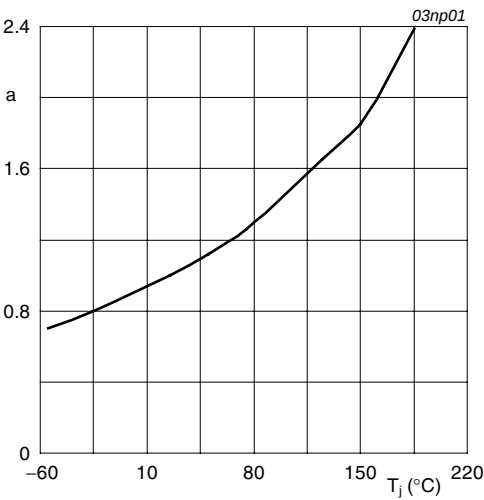
$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 9. Gate-source threshold voltage as a function of junction temperature



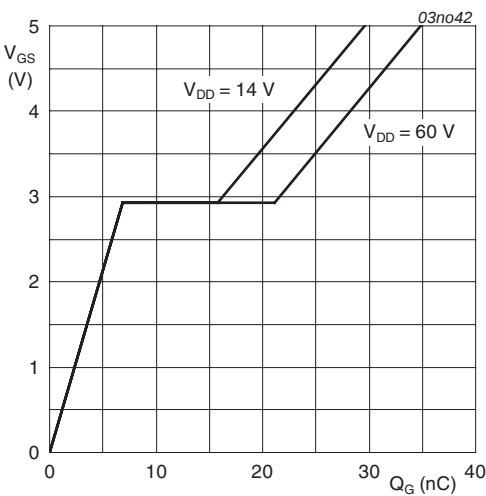
$$T_j = 25^{\circ}C; t_p = 300\mu s$$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DS(on)}}{R_{DS(on)25^{\circ}C}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$$T_j = 25^{\circ}C; I_D = 25A$$

Fig 12. Gate-source voltage as a function of turn-on gate charge; typical values

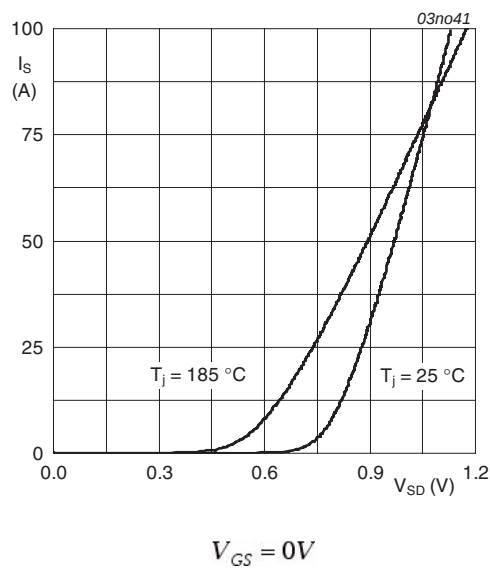


Fig 13. Source current as a function of source-drain voltage; typical values

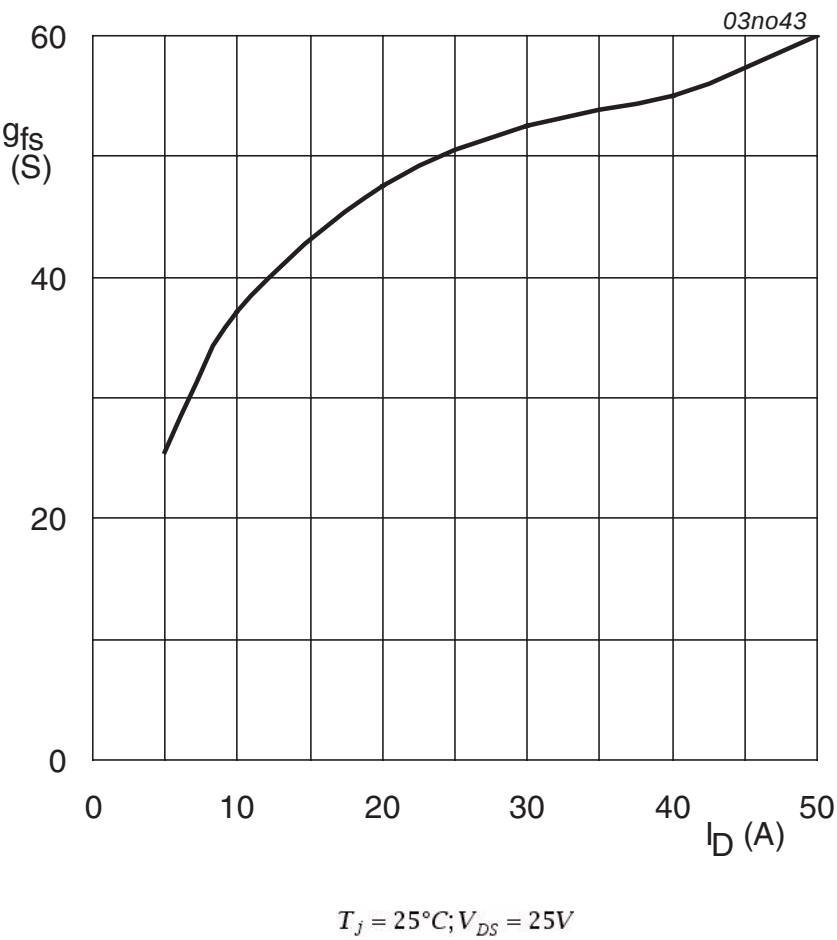
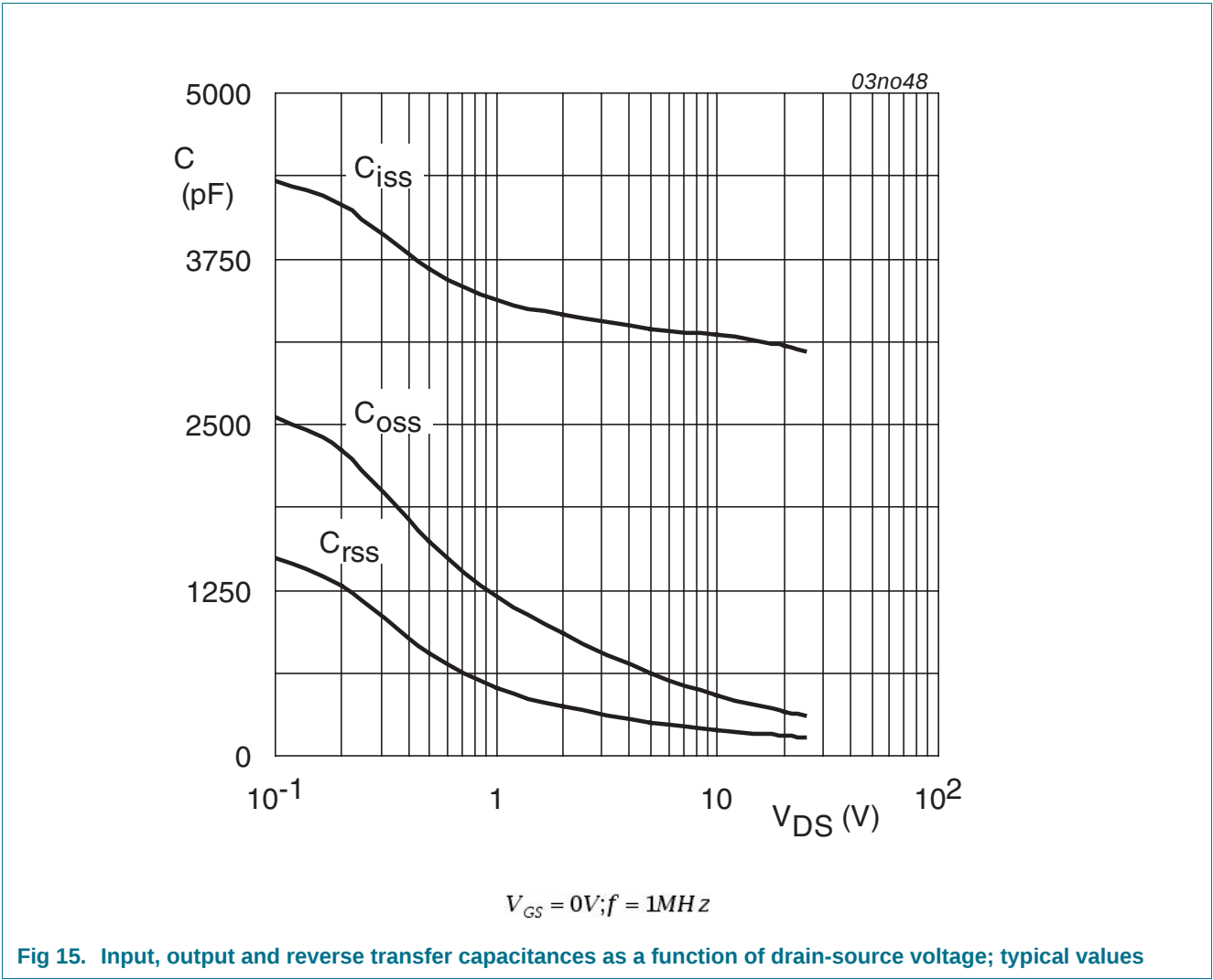


Fig 14. Forward transconductance as a function of drain current; typical values



7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

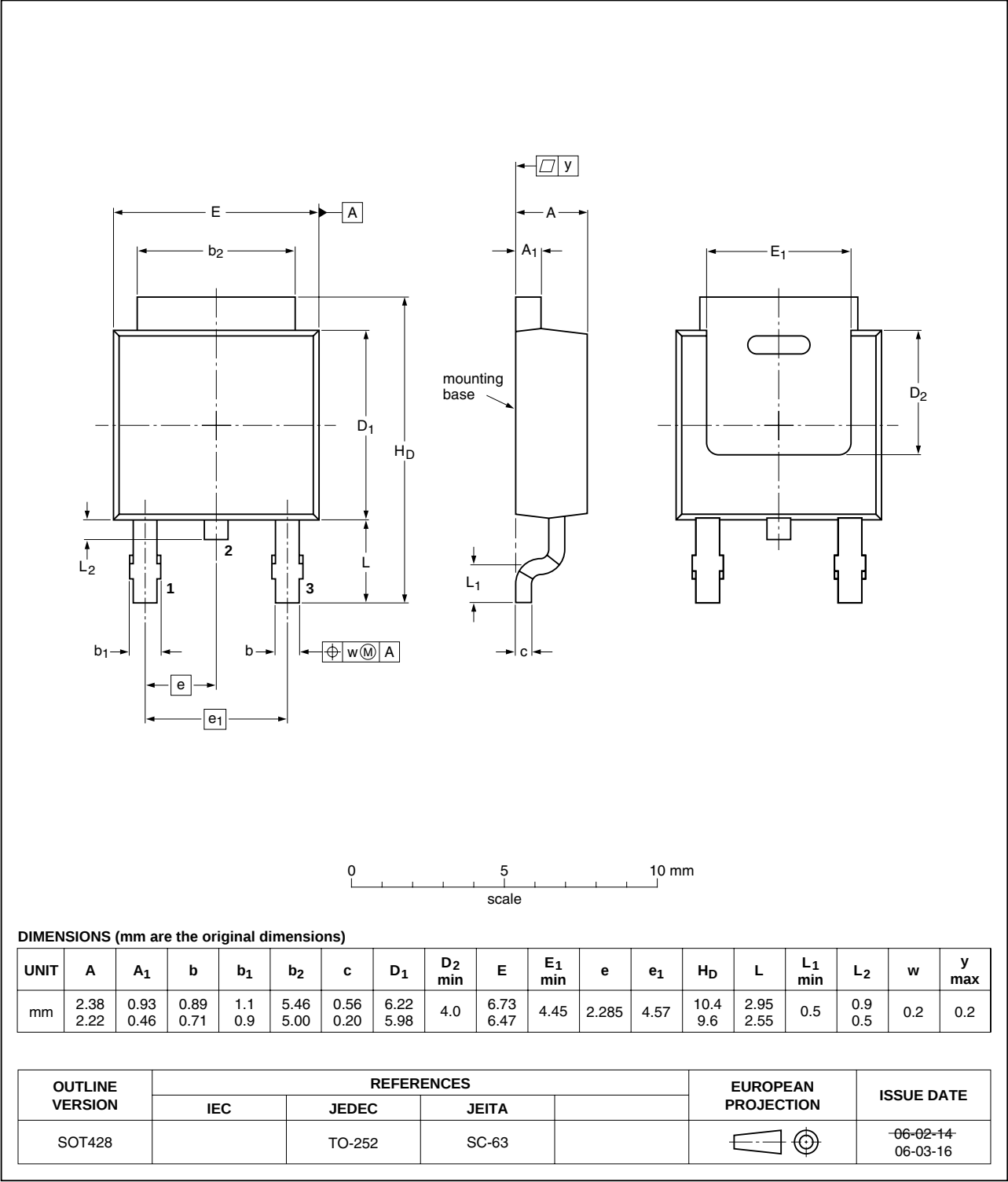


Fig 16. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9217-75B v.2	20110203	Product data sheet	-	BUK9217_75B v.1
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate.			
BUK9217_75B v.1	20040122	Product data	-	-

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9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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